

8930

High productivity patterned wafer inspection system detects a wide variety of critical defects that affect the yield and reliability of wide bandgap (WBG) semiconductors, such as SiC and GaN

BENEFITS:

The 8930 provides high throughput, inline defect detection and binning, helping power semiconductor and RF device makers:

- Accurately identify and quickly resolve production process issues that can affect final chip yield and quality
- Implement high sampling strategies by monitoring up to 100% of die on all wafers at critical process steps to remove die that may fail at package-level testing or in field use to automotive standards
- Produce power application products on an extendible, cost-effective platform that provides the inspection sensitivity and AI technology needed to isolate critical defects and the throughput to support high sampling

TECHNOLOGIES:

- Multi-mode LED scanning capability with high NA optics
- High throughput operating modes
- Transparent wafer handling; patterned and unpatterned wafer inspection
- DefectWise® DL-based defect discovery and binning technology
- DesignWise® and FlexPoint™ precise area inspection technologies
- Advanced defect detection and noise suppression algorithms

APPLICATIONS:

- Epi substrate quality control of SiC/GaN substrate defectivity
- Inline process and tool monitoring with high sampling for reduced excursion risk
- SiC critical detection of threading dislocations and reliability defects
- Outgoing quality control of final patterned wafers





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Power Semiconductor and RF Devices
Automotive and EV/HEV
Clean Energy

PLATFORM:

- Customizable configurations
- Extendible
- Upgradeable

WAFER SIZES:

- 300mm
- **200mm**
- 150mm